# PEMB10; PUMB10

# PNP/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

Rev. 3 — 3 January 2012

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

PNP/PNP Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number			NPN/PNP	NPN/NPN	Package
	NXP	JEITA	complement	complement	configuration
PEMB10	SOT666	-	PEMD10	PEMH10	ultra small and flat lead
PUMB10	SOT363	SC-88	PUMD10	PUMH10	very small

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



## 2. Pinning information

Table 3. Pinning

Table 3.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		R <sub>1</sub> R <sub>2</sub>
4	GND (emitter) TR2		$\parallel \parallel $
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	1 2 3
			006aaa212

## 3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMB10	<b>'-</b>	plastic surface-mounted package; 6 leads	SOT666
PUMB10	SC-88	plastic surface-mounted package; 6 leads	SOT363

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMB10	Z5
PUMB10	B*0

[1] \* = placeholder for manufacturing site code.

## 5. Limiting values

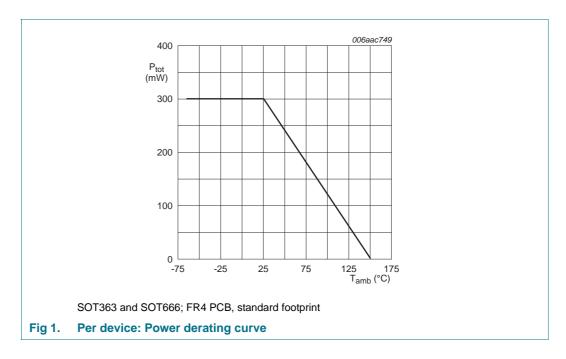
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	<b>-5</b>	V
VI	input voltage				
	positive		-	+5	V
	negative		-	-12	V
Io	output current		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25 ^{\circ}C$	<u>[1]</u>		
	PEMB10 (SOT666)		[2] _	200	mW
	PUMB10 (SOT363)		-	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25 ^{\circ}C$	<u>[1]</u>		
	PEMB10 (SOT666)		[2] _	300	mW
	PUMB10 (SOT363)		-	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



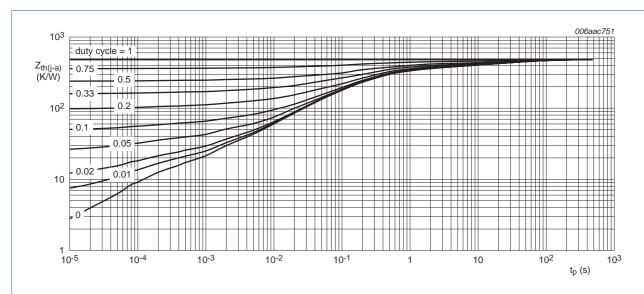
#### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMB10 (SOT666)		[2] _	-	625	K/W
	PUMB10 (SOT363)		-	-	625	K/W
Per device						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMB10 (SOT666)		[2] _	-	417	K/W
	PUMB10 (SOT363)		-	-	417	K/W

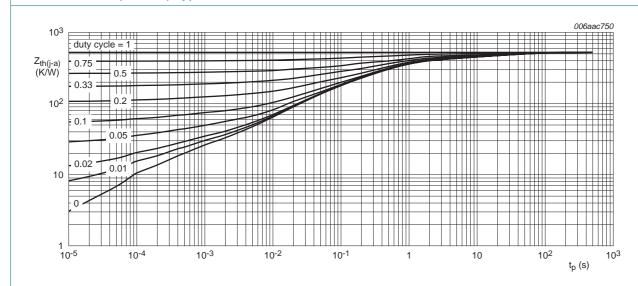
<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB10 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB10 (SOT363); typical values

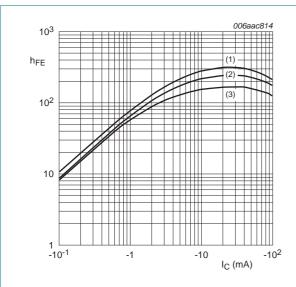
## 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
OLO	collector-emitter	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-100	nA
	cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-180	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-0.6	-0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$	-1.1	-0.75	-	V
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CB} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ f = 100 MHz	[1] -	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor.



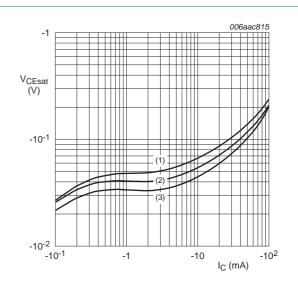
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 4. DC current gain as a function of collector current; typical values



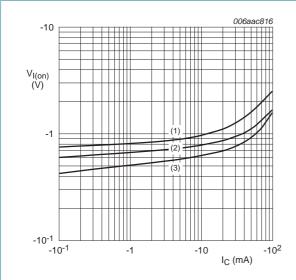
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



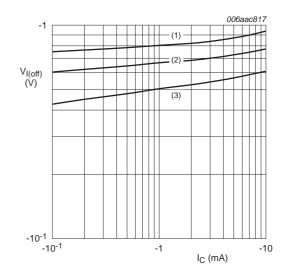


(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 6. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 7. Off-state input voltage as a function of collector current; typical values

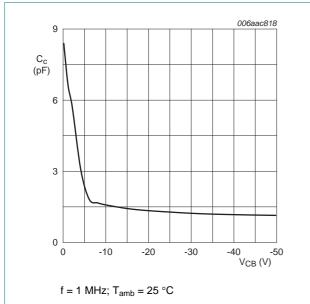


Fig 8. Collector capacitance as a function of collector-base voltage; typical values

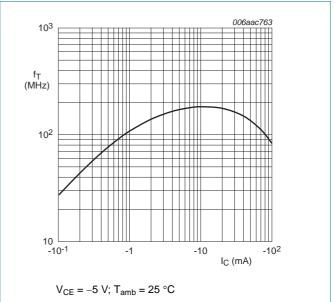


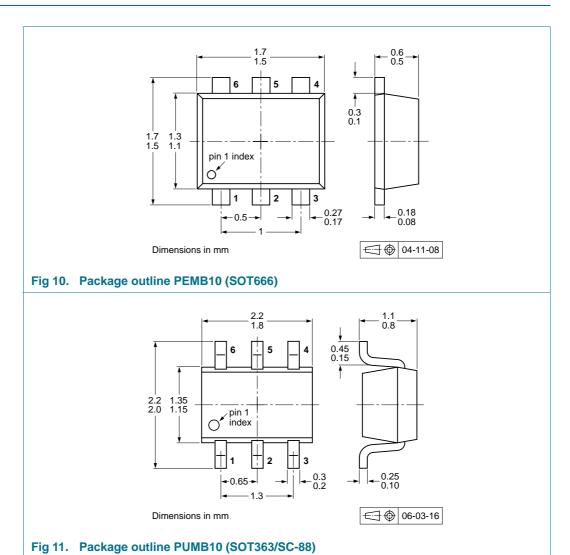
Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Packing information

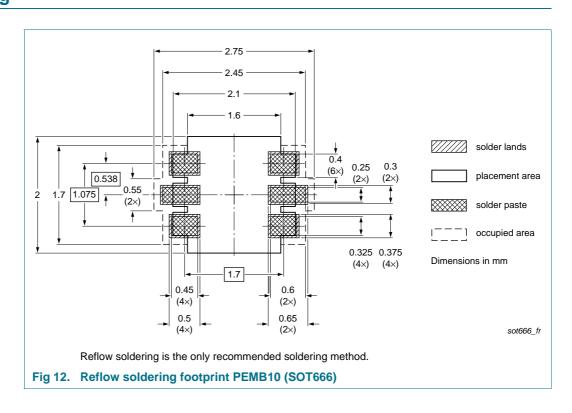
Table 9. Packing methods

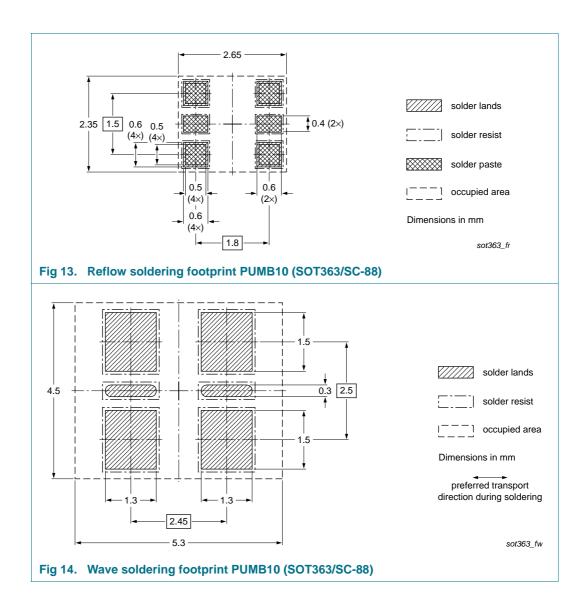
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

		3.					
Type number	Package	Description		Packii	ng quai	ntity	
				3000	4000	8000	10000
PEMB10	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMB10	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

## 11. Soldering





PNP/PNP resistor-equipped transistors; R1 = 2.2 kΩ, R2 = 47 kΩ

## 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
PEMB10_ PUMB10 v.3	20120103	Product data sheet	-	PEMB10_ PUMB10 v.2				
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>							
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>							
	Section 1 "Product profile": updated							
	Section 4 "Marking": updated							
	<ul> <li><u>Table 7 "Thermal characteristics"</u>: updated according to the latest measurements</li> </ul>							
	<ul> <li><u>Table 8 "Characteristics"</u>: I<sub>CEO</sub> updated according to the latest measurements, f<sub>T</sub> added, V<sub>i(off)</sub> redefined to V<sub>I(off)</sub> off-state input voltage, V<sub>i(on)</sub> redefined to V<sub>I(on)</sub> on-state input voltage.</li> </ul>							
	• Figure 1 to 9: added							
	Section 8 "Test information": added							
	<ul> <li><u>Figure 10</u> and <u>11</u>: replaced by minimized package outline drawings</li> <li><u>Section 10 "Packing information"</u>: added</li> <li><u>Section 11 "Soldering"</u>: added</li> </ul>							
	Section 13 "Legal information": updated							
PEMB10_ PUMB10 v.2	20031003	Product data sheet	-	PEMB10 v.1				
PEMB10 v.1	20010914	Preliminary specification	on -	-				

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#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PEMB10; PUMB10

PNP/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

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